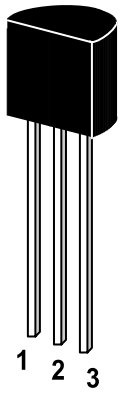
ST 2SC3876

NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y and according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Base Current	I_B	50	mA
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	125	^{O}C
Storage Temperature Range	T_S	-55 to +125	^{O}C

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at V_{CE}=1V, I_C=100mA					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
at V_{CE}=6V, I_C=400mA	h_{FE}	25	-	-	-
Collector Cutoff Current					
at V_{CB}=35V	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current					
at V_{EB}=5V	I_{EBO}	-	-	0.1	μA
Collector Emitter Saturation Voltage					
at I_C=100mA, I_B=10mA	$V_{CE(sat)}$	-	0.1	0.25	V
Transition Frequency					
at V_{CE}=6V, I_C=20mA	f_T	-	300	-	MHz
Base Emitter Voltage					
at I_C=100mA, V_{CE}=1V	V_{BE}	-	0.8	1	V
Collector Output Capacitance					
at V_{CB}=6V, f=1MHz	C_{OB}	-	7	-	pF